

1200V SiC Schottky Diode

VDC	1200 V
Q _C	269 nC
I _F	50 A
T _{j,max}	175 °C

Amp+™ Features

- Unipolar rectifier with surge current
- Zero reverse recovery current
- Fast, temperature-independent switching
- Avalanche tested to 666mJ*
- All parts tested to greater than 1,400V

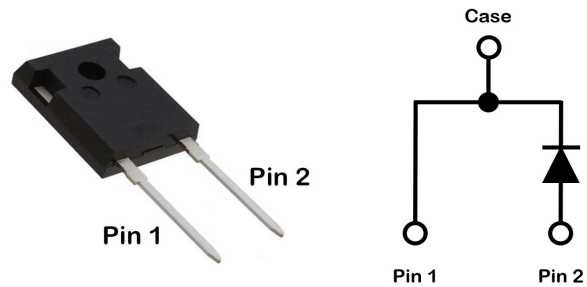
Amp+™ Benefits

- Near zero switching loss
- Higher efficiency
- Smaller heat sink
- Easy to parallel

Amp+™ Applications

- Solar Inverters
- Switch mode power supplies, UPS
- Power factor correction
- EV charging stations

Package



Part #	Package	Marking
GP3D050A120B	TO-247-2L	3D050A120



Maximum Ratings, at T_j=25 °C, unless otherwise specified

Characteristics	Symbol	Conditions	Values	Unit
Continuous forward current	I _F **	T _C =25 °C, T _J =175 °C	136	A
		T _C =125 °C, T _J =175 °C	74	
		T _C =150 °C, T _J =175 °C	48	
Surge non-repetitive forward current sine halfwave	I _{FSM}	T _C =25 °C, t _p =8.3 ms	390	A
		T _C =110 °C, t _p =8.3 ms	340	
Non-repetitive peak forward current	I _{F,max}	T _C =25 °C, t _p =10 μs	2000***	A
i ² t value	∫i ² dt	T _C =25 °C, t _p =8.3 ms	631	A ² s
		T _C =110 °C, t _p =8.3 ms	480	
Repetitive peak reverse voltage	V _{RRM}	T _J =25 °C	1200	V
Diode dv/dt ruggedness	dv/dt	Turn-on slew rate, repetitive	200	V/ns
Power dissipation	P _{tot} **	T _C =25 °C	600	W
Operating junction & storage temperature	T _j , T _{storage}	Continuous	-55...175	°C
Soldering temperature	T _{solder}	Wave soldering leads	260	°C
Mounting torque		M3 Screw	1	N-m

Notes:

* EAS of 666 mJ is based on starting T_j = 25°C, L = 1.0 mH, I_{AS} = 36.50 A, V = 50 V.

** Typical R_{thJC} used

*** Limited by testing equipment

Electrical Characteristics, at T_j=25 °C, unless otherwise specified

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
DC blocking voltage	V _{DC}	T _j =25 °C	1200	-	-	V
Breakdown voltage	V _{BR}	I _R =2.00mA, T _j =25 °C	1400	-	-	V
Diode forward voltage	V _F	I _F =50A, T _j =25 °C	-	1.50	1.70	V
		I _F =50A, T _j =125 °C	-	1.82	-	
		I _F =50A, T _j =175 °C	-	2.10	2.70	
Reverse current	I _R	V _R =1,200V, T _j =25 °C	-	6	100	μA
		V _R =1,400V, T _j =25 °C	-	35	-	
		V _R =1,200V, T _j =125 °C	-	49	-	
		V _R =1,200V, T _j =175 °C	-	193	750	
Total capacitive charge	Q _C	V _R =800V, T _j =25 °C	-	269	-	nC
Total capacitance	C	V _R =1V, f=1 MHz	-	3040	-	pF
		V _R =400V, f=1 MHz	-	253	-	
		V _R =800V, f=1 MHz	-	181	-	

Thermal Characteristics

Characteristics	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal resistance, junction-case	R _{thJC}	-	-	0.25	0.35	°C/W

Typical Performance

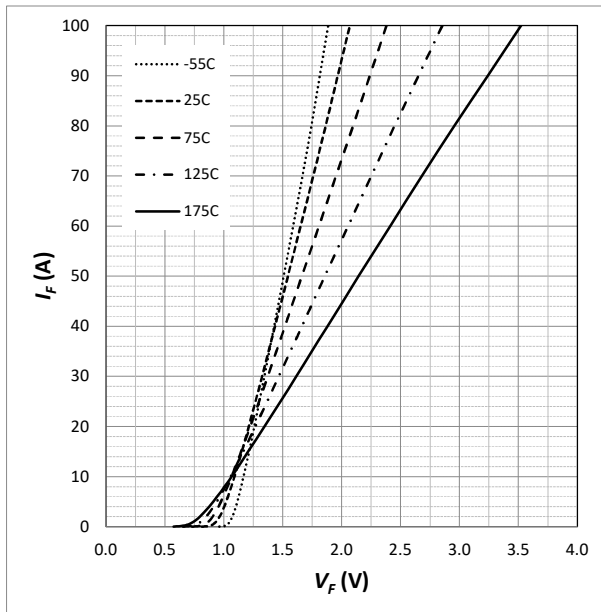


Fig. 1 Forward Characteristics (parameterized on T_j)

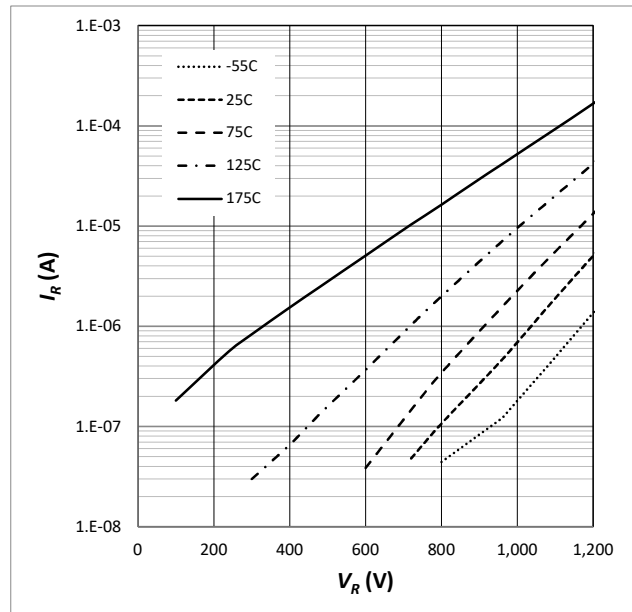


Fig. 2 Reverse Characteristics (parameterized on T_j)

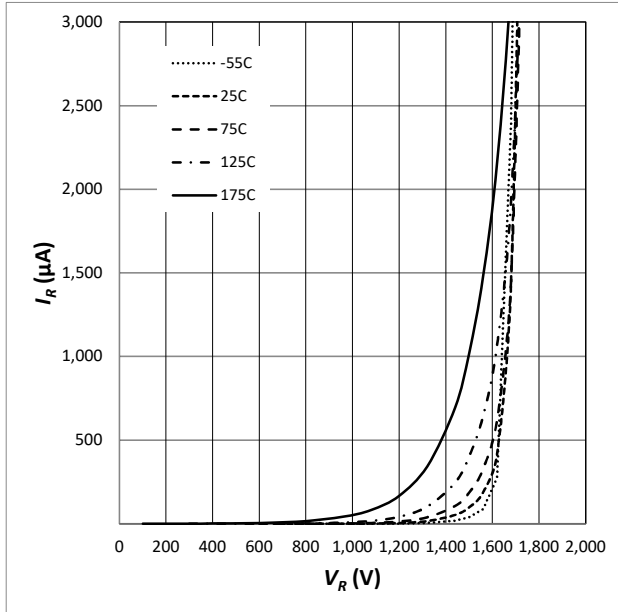


Fig. 3 Reverse Characteristics (parameterized on T_j)

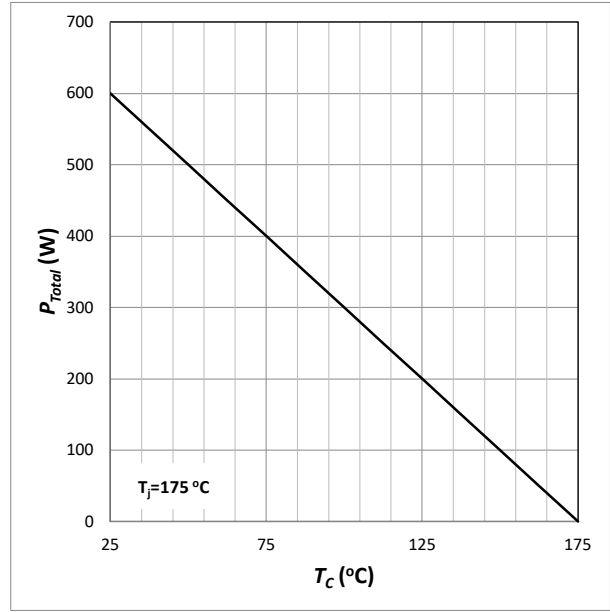


Fig. 4 Power Derating

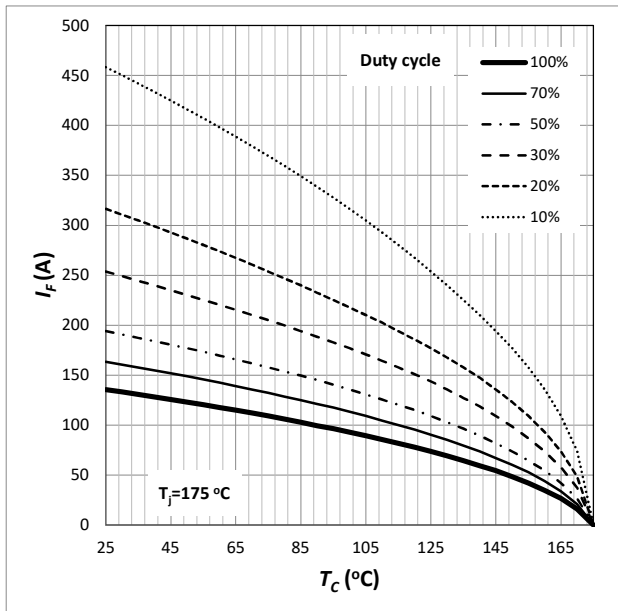


Fig. 5 Capacitance

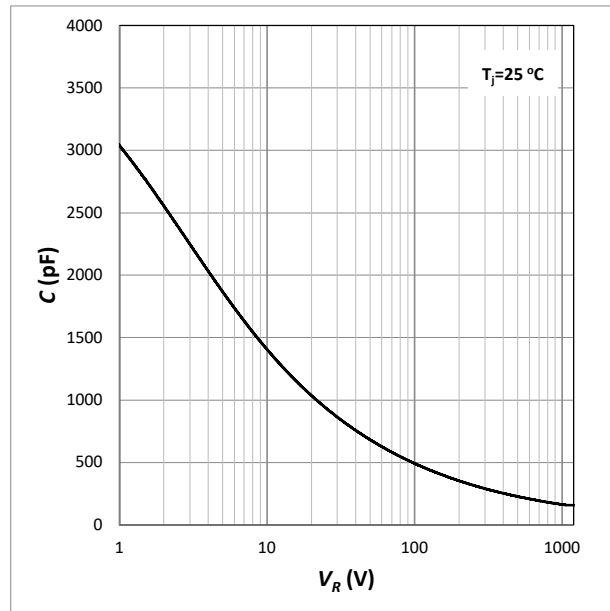


Fig. 6 Capacitance

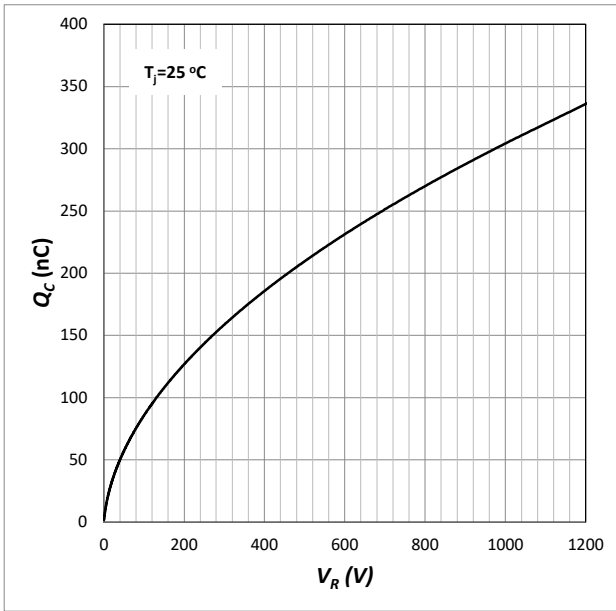


Fig. 7 Capacitive Charge

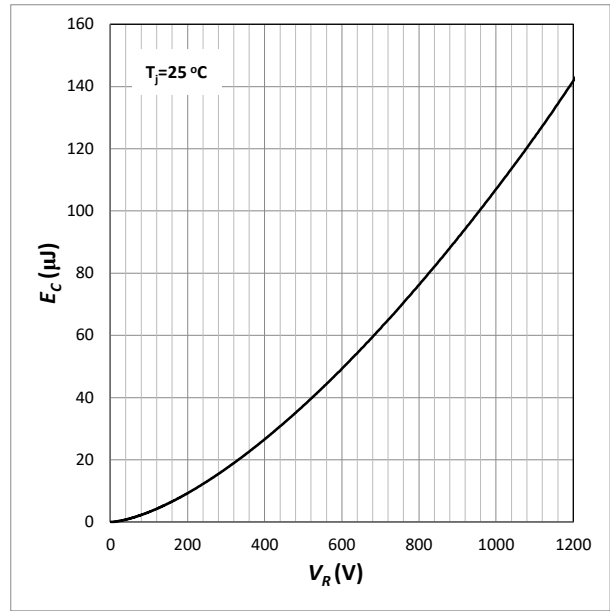


Fig. 8 Typical Capacitance Stored Energy

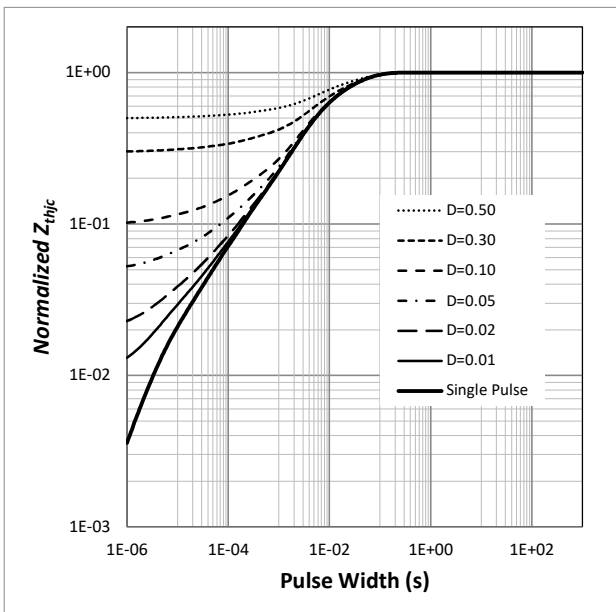


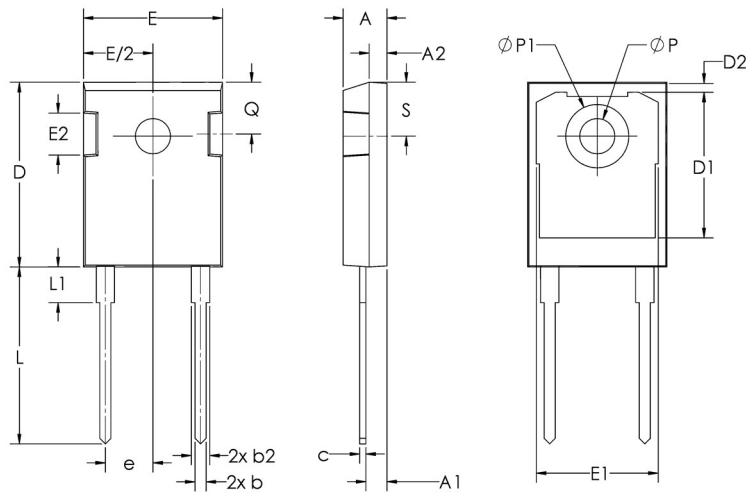
Fig. 9 Transient Thermal Impedance

1200V SiC Schottky Diode

Amp+™

GP3D050A120B

Package Dimensions TO-247-2L



Sym	Millimeters		Inches	
	Min	Max	Min	Max
A	4.70	5.31	0.185	0.209
A1	2.21	2.59	0.087	0.102
A2	1.50	2.49	0.059	0.098
b	0.99	1.40	0.039	0.055
b2	1.65	2.39	0.065	0.094
c	0.38	0.89	0.015	0.035
D	20.80	21.46	0.819	0.845
D1	13.08	17.65	0.515	0.695
D2	0.51	1.35	0.020	0.053
E	15.49	16.26	0.610	0.640
E1	13.46	14.16	0.530	0.557
E2	3.43	5.49	0.135	0.216
e	5.44 BSC		.214 BSC	
L	19.81	20.32	0.780	0.800
L1	4.10	4.50	0.161	0.177
ØP	3.56	3.66	0.140	0.144
ØP1	7.06	7.39	0.278	0.291
Q	5.38	6.20	0.212	0.244
S	6.04	6.30	0.238	0.248

Notes

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented March, 2013. RoHS Declarations for this product can be obtained from the Product Documentation sections of www.SemiQ.com.

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